

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING
APPARATUS

ABSTRACT

A technique includes (a) preparing a substrate including a first region, which forms an outer surface of a recess and is adjacent to an opening of the recess and whose surface is terminated by a first termination, and a second region, which forms an inner surface of the recess and whose surface is terminated by the first termination; and (b) removing the first termination in the first region by exposing the substrate to a first processing solution containing a liquid that reacts with the first termination, so that a density of the first termination in the first region is smaller than a density of the first termination in the second region.

Figs. 7B and 7C